



2N7002W

N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

Features

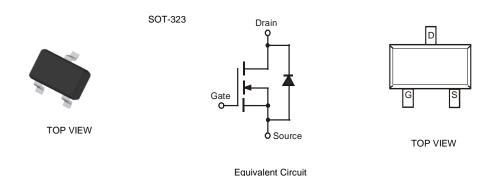
- Low-On Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q101, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at

https://www.diodes.com/products/automotive/automotive-products/.

- This part is qualified to JEDEC standards (as references in AEC-Q101) for High Reliability.
- https://www.diodes.com/quality/product-definitions/

Mechanical Data

- Case: SOT-323
- Case Material: Molded Plastic, "Green" Molding Compound, Note 4. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish Matte Tin annealed over Alloy 42 leadframe. Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Weight: 0.006 grams (approximate)



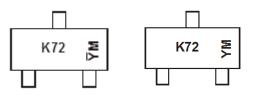
Ordering Information (Note 4)

Part Number	Case	Packaging
2N7002W-7-F	SOT-323	3000/Tape & Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



K72 = Product Type Marking Code

YM = Date Code Marking for SAT (Shanghai Assembly/ Test site)

 $\overline{Y}M$ = Date Code Marking for CAT (Chengdu Assembly/ Test site) Y or \overline{Y} = Year (ex: A = 2013)

M = Month (ex: 9 = September)

Chengdu A/T Site Shanghai A/T Site

Date Code Key

Year	2012	2	2013		2014	20	15	2016		2017	2	2018
Code	Z		Α		В	(\circ	D		Е		F
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteris	etic	Symbol	Value	Unit
Drain-Source Voltage		V _{DSS}	60	V
Drain-Gate Voltage $R_{GS} \le 1.0 M\Omega$		V_{DGR}	60	V
Gain-Source Voltage	Continuous Pulsed	V_{GSS}	±20 ±40	V
Drain Current (Note 5)	Continuous Continuous @ +100°C Pulsed	I _D	115 73 800	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	D	200	mW
Derating above T _A = +25°C	P_{D}	1.60	mW
Thermal Resistance, Junction to Ambient	$R_{ hetaJA}$	625	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

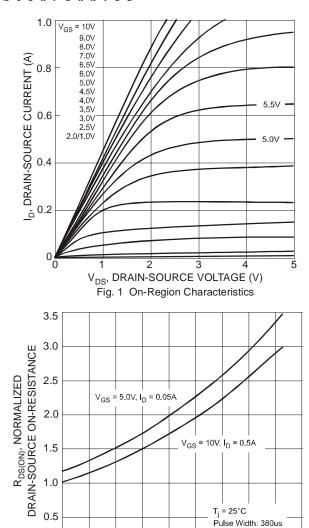
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)					•	
Drain-Source Breakdown Voltage	BV _{DSS}	60	70	_	V	$V_{GS} = 0V, I_D = 10\mu A$
Zero Gate Voltage Drain Current @ $T_C = +25$ °C @ $T_C = +125$ °C	I _{DSS}	_	_	1.0 500	μА	V _{DS} = 60V, V _{GS} = 0V
Gate-Body Leakage	I _{GSS}	_	_	±10	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	$V_{GS(th)}$	1.0	_	2.0	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$
Static Drain-Source On-Resistance @ $T_J = +25$ °C			1.8	7.5	Ω	$V_{GS} = 5.0V, I_D = 0.05A$
@ T _j = +125°C	R _{DS(ON)}	_	2.6	13.5	12	$V_{GS} = 10V, I_D = 0.5A$
On-State Drain Current	I _{D(ON)}	0.5	1.0	_	Α	$V_{GS} = 10V, V_{DS} = 7.5V$
Forward Transconductance	g _{FS}	80	_	_	mS	$V_{DS} = 10V, I_D = 0.2A$
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	C _{iss}		22	50	pF	V 05V V 0V
Output Capacitance Reverse Transfer Capacitance		_	11	25	pF	V _{DS} = 25V, V _{GS} = 0V f = 1.0MHz
		_	2.0	5.0	pF	1 = 1.0WI 12
SWITCHING CHARACTERISTICS (Note 7)					•	
Turn-On Delay Time	t _{D(ON)}		7.0	20	ns	$V_{DD} = 30V, I_D = 0.2A,$
Turn-Off Delay Time	t _{D(OFF)}	_	11	20	ns	$R_L = 150\Omega$, $V_{GEN} = 10V$, $R_{GEN} = 25\Omega$

Notes:

- 5. Device mounted on FR-4 PCB 1.0 x 0.75 x 0.062 inch pad layout as shown on Diodes, Inc. suggested pad layout AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
- 6. Short duration pulse test used to minimize self-heating effect.
- 7. Guaranteed by design. Not subject to production testing.

 $T_i = 25^{\circ}C$





DRAIN-SOURCE ON-RESISTANCE R_{DS(ON)}, NORMALIZED V_{GS} = 5.0V $V_{GS} = 10V$ 0 0 0.2 0.4 0.6 0.8 1.0 I_D, DRAIN CURRENT (A) Fig. 2 On-Resistance vs. Drain Current 6 DRAIN-SOURCE ON-RESISTANCE R_{DS(ON)}, NORMALIZED I_D = 50mA

8 10

 $V_{\rm GS}$, GATE TO SOURCE VOLTAGE (V)

Fig. 4 On-Resistance vs. Gate-Source Voltage

12

T_J, JUNCTION TEMPERATURE (°C) Fig. 3 On-Resistance vs. Junction Temperature

70 95

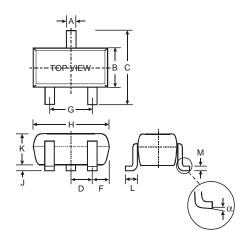
20 45

120 145 170

Package Outline Dimensions

0.0 <u></u>-55

Please see http://www.diodes.com/package-outlines.html for the latest version.



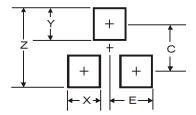
SOT-323					
Dim	Min	Max			
Α	0.25	0.40			
В	1.15	1.35			
С	2.00	2.20			
D	0.65 N	ominal			
F	0.30	0.40			
G	1.20	1.40			
Н	1.80	2.20			
J	0.0	0.10			
K	0.90	1.00			
L	0.25	0.40			
M	0.10	0.18			
α	0°	8°			
All Di	All Dimensions in mm				

0



Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
Z	2.8
Х	0.7
Υ	0.9
С	1.9
E	1.0

IMPORTANT NOTICE

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel. Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes Incorporated.

LIFE SUPPORT

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

- A. Life support devices or systems are devices or systems which:
 - 1. are intended to implant into the body, or
 - 2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.
- B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

Copyright © 2019, Diodes Incorporated

www.diodes.com

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for MOSFET category:

Click to view products by Diodes Incorporated manufacturer:

Other Similar products are found below:

614233C 648584F IRFD120 JANTX2N5237 FCA20N60_F109 FDZ595PZ 2SK2545(Q,T) 405094E 423220D TPCC8103,L1Q(CM MIC4420CM-TR VN1206L 614234A 715780A NTNS3166NZT5G SSM6J414TU,LF(T 751625C IPP110N20N3GXK BUK954R8-60E NTE6400 SQJ402EP-T1-GE3 2SK2614(TE16L1,Q) DMN1017UCP3-7 EFC2J004NUZTDG ECH8691-TL-W FCAB21350L1 P85W28HP2F-7071 DMN1053UCP4-7 NTE221 NTE222 NTE2384 NTE2941 NTE2945 NTE2946 NTE2960 NTE2969 NTE2976 NTE6400A NTE2916 NTE2956 NTE2911 DMN2080UCB4-7 TK10A80W,S4X(S STF35N65DM2 STW70N60DM6-4 SSM6P54TU,LF SSM6P69NU,LF DMP22D4UFO-7B DMN1006UCA6-7 DMN16M9UCA6-7